

ABSTRACT OF THE DISCLOSURE

ANNEALING PROCESS AND DEVICE OF SEMICONDUCTOR WAFER

A device and method for annealing a wafer. The preferred embodiment includes applying a basic thermal budget to a weakened zone of a wafer, substantially evenly over the weakened zone. The basic thermal budget is insufficient to detach a detachment layer from a remainder of the wafer at the weakened zone. An additional 5 thermal budget is applied locally in an initiation region of the weakened zone to initiate the detachment of the detachment layer at the weakened zone.